



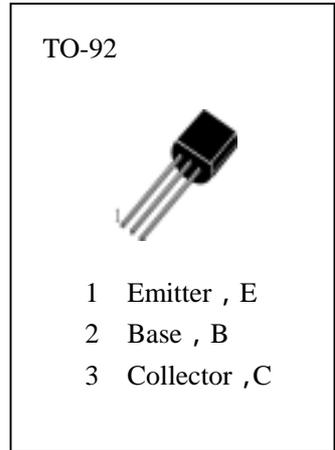
AMPLIFIER TRANSISTOR

Collector-Emitter Voltage:Vceo=150V.

Collector Dissipation:Pc(max)=625mW

ABSOLUTE MAXIMUM RATINGS (Ta=25)

- T_{stg}——Storage Temperature..... -55~150
- T_j——Junction Temperature..... 150
- P_C——Collector Dissipation.....625mW
- V_{CBO}——Collector-Base Voltage.....-160V
- V_{CEO}——Collector-Emitter Voltage.....-150V
- V_{EBO}——Emitter-Base Voltage.....-5V
- I_C——Collector Current.....-600mA



ELECTRICAL CHARACTERISTICS (Ta=25)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	-160			V	I _C =-100 μ A, I _E =0
BVCEO	Collector-Emitter Breakdown Voltage	-150			V	I _C =-1mA, I _B =0
BVEBO	Emitter-Base Breakdown Voltage	-5			V	I _E =-10 μ A , I _C =0
ICBO	Collector Cut-off Current			-50	nA	V _{CB} =-120V, I _E =0
IEBO	Emitter-Base Cut-off Current			-50	nA	V _{EB} =-3V, I _C =0
HFE (1)	DC Current Gain	30				V _{CE} =-5V, I _C =-1mA
HFE (2)		60		280		V _{CE} =-5V, I _C =-10mA
HFE (3)		50				V _{CE} =-5V, I _C =-50mA
VCE(sat1)	Collector- Emitter Saturation Voltage			-0.2	V	I _C =-10mA, I _B =-1mA
VCE(sat2)				-0.5	V	I _C =-50mA, I _B =-5mA
VBE(sat1)	Base-Emitter Saturation Voltage			-1	V	I _C =-10mA, I _B =-1mA
VBE(sat2)				-1	V	I _C =-50mA, I _B =-5mA,
fT	Current Gain-Bandwidth Product	100		400	MHZ	V _{CE} =-10V, I _C =-10mA F=100MHZ